NPN Silicon RF power transistor MRF426

Description:
MRF426 is designed primarily for high gain driver and output linear amplifier stages in 1.5 to 30 MHz HF/SSB equipment. **BLX 13 Equivalent**

Features:
Specified 28 Volt, 30 MHz Characteristics:
Output Power = 25 W (PEP), Minimum Gain = 22 dB, Efficiency = 35%
Intermodulation Distortion @ 25 W (PEP), IMD = –30 dB (Max)

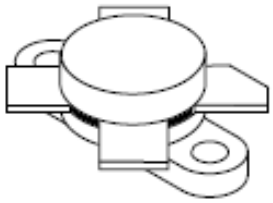
Maximum Ratings at T_U = 25℃

Symbol	Test Conditions	Characteristics		Units
BVCES	IC=10 mA	Max.	65	V
BVCEO	IC=30 mA	Max.	35	V
BVEBO	IE=5 mA	Max.	4	V
IC		Max.	3	A
Ptot		Max.	70	W
TSTG		Min.	-65	℃
		Max.	150	℃
TjM		Max.	200	℃

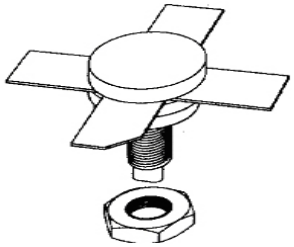
Characteristics at T_U = 25℃ (VCC =28 V f=30 MHz)

Symbol	Test Conditions	Characteristics		Units
Pout		Typ.	25PEP	W
GP		Typ.	20	dB
η		Typ.	40	%
hFE	IC = 1.3A VCE =10V	Typ.	50	
VCEsat	IC = 4A IB =0.8 A	Max.	1.5	V
ICES	VCE =36V	Max.	10	mA
CCBO	VCB =28V	Typ.	100	pF
d3		Max.	＜-30	dB

Drawings:



CASE211-07 **or**



SOT120 or SOT123